



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re application of

NANDAKUMAR

Serial No. 09/252,514 (TI-23103)

Filed February 18, 1999

For: DUAL-COUNTERDOPED CHANNEL FIELD EFFECT TRANSISTOR AND METHOD

Art Unit 2811

Examiner S. Crane

Commissioner for Patents  
Washington, D. C. 20231

Sir:

**AMENDMENT UNDER 37 C.F.R. 1.116**

In response to the Office action dated September 28, 2001, please amend the above identified application as follows:

**In the specification:**

Cancel the prior amendment to the paragraph on page 6, lines 22 to 34 and replace by amendment as follows:

"Referring to FIGURE 1E, n-type [source/drain] regions 34 are formed [around] within p-type source/drain pockets 32 using ion implantation. In this example, [source/drain] regions 34 are implanted with an n-type material such as arsenic.. Although source/drain pockets 32 are shown extending around [and within source/drain] regions 34 and adjoining isolation trenches 20, it will be understood that source/drain pockets 32 may extend only along the inside portion of

TC 2800 MAIL ROOM

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